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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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semiconductors may lead to personal injury, fire or property damage.
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measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or
(iii) prevention against any malfunction or mishap.

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Hex Bus Drivers (with 3-state outputs)



ADE-205-495 (Z) 1st. Edition Sep. 2000

Features

• High Speed Operation: t_{pd} (A to Y) = 9 ns typ ($C_L = 50 \text{ pF}$)

• High Output Current: Fanout of 15 LSTTL Loads

• Wide Operating Voltage: $V_{CC} = 2$ to 6 V

Low Input Current: 1 μA max

• Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)

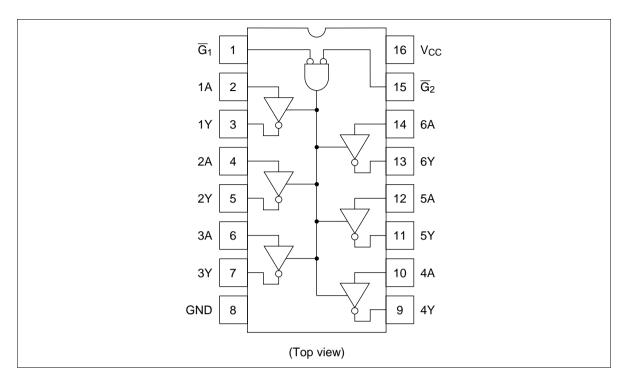
Function Table

Inputs			Output	
G₁	$\overline{G_{\scriptscriptstyle 2}}$	Α	Υ	
Н	X	X	Z	
X	Н	X	Z	
L	L	Н	L	
L	L	L	Н	

X: irrelevant

Z : Off (high-impedance) state of a 3-state output.

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Rating	Unit	
Supply voltage range	V _{cc}	-0.5 to +7.0	V	
Input voltage	V_{IN}	-0.5 to V_{cc} + 0.5	V	
Output voltage	V _{out}	-0.5 to $V_{cc} + 0.5$	V	
DC current drain per pin	I _{OUT}	±35	mA	
DC current drain per V _{cc} , GND	I _{CC} , I _{GND}	±75	mA	
DC input diode current	I _{IK}	±20	mA	
DC output diode current	I _{OK}	±20	mA	
Power dissipation per package	P _T	500	mW	
Storage temperature	Tstg	-65 to +150	°C	

DC Characteristics

			Ta = 25°C		+85°C					
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Condition	าร
Input voltage	V _{IH}	2.0	1.5	_	_	1.5	_	V		
		4.5	3.15	_	_	3.15	_	_		
		6.0	4.2	_	_	4.2	_	=		
	V _{IL}	2.0	_	_	0.5	_	0.5	V		
		4.5	_	_	1.35	_	1.35	=		
		6.0	_	_	1.8	_	1.8	=		
Output voltage	V _{OH}	2.0	1.9	2.0	_	1.9	_	V	$Vin = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20 \mu A$
		4.5	4.4	4.5	_	4.4	_	=		
		6.0	5.9	6.0	_	5.9	_	=		
		4.5	4.18	_	_	4.13	_	=		$I_{OH} = -6 \text{ mA}$
		6.0	5.68	_	_	5.63	_	=		$I_{OH} = -7.8 \text{ mA}$
	V _{OL}	2.0	_	0.0	0.1	_	0.1	V	$Vin = V_{IH} \text{ or } V_{IL}$	I _{OL} = 20 μA
		4.5	_	0.0	0.1	_	0.1	_		
		6.0	_	0.0	0.1	_	0.1	_		
		4.5	_	_	0.26	_	0.33	_		I _{OL} = 6 mA
		6.0	_	_	0.26	_	0.33	_		I _{OL} = 7.8 mA
Off-state output current	l _{oz}	6.0	_	_	±0.5	_	±5.0	μΑ	$Vin = V_{IH} \text{ or } V_{IL},$ $Vout = V_{CC} \text{ or } C$	
Input current	lin	6.0	_	_	±0.1	_	±1.0	μΑ	Vin = V _{cc} or GND	
Quiescent supply current	I _{cc}	6.0	_	_	4.0	_	40	μΑ	Vin = V_{CC} or GND, lout = 0 μ A	

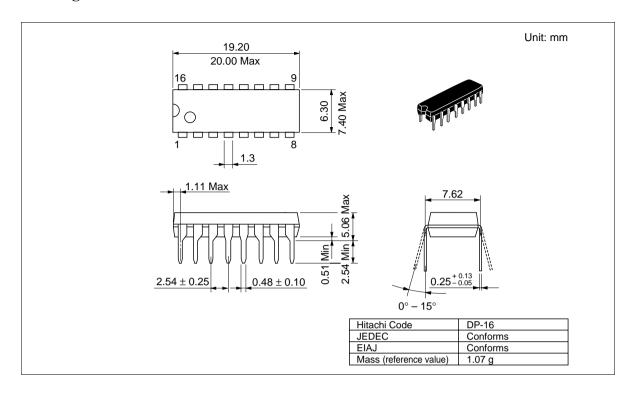
Ta = -40 to

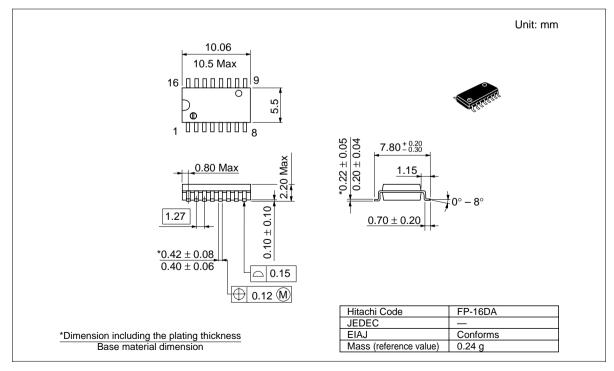
AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Ta = -40 to $Ta = 25^{\circ}C$ +85°C

Item	Symbol	V_{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Propagation delay	t _{PLH}	2.0	_	_	95	_	120	ns	
time	$t_{\tiny PHL}$	4.5	_	9	19	_	24		
		6.0	_	_	16	_	20	_	
Output enable	t _{zH}	2.0	_	_	220	_	275	ns	
time	t_{zL}	4.5	_	13	44	_	55	_	
		6.0	_	_	37	_	47	=	
Output disable	t _{HZ}	2.0	_	_	220	_	275	ns	
time	t_{LZ}	4.5	_	15	44	_	55	_	
		6.0	_	_	37	_	47	=	
Output rise/fall	t _{TLH}	2.0	_	_	60	_	75	ns	
time	t_{THL}	4.5	_	4	12	_	15	=	
		6.0	_	_	10	_	13	=	
Input capacitance	Cin	_	_	5	10	_	10	pF	

Package Dimensions





Unit: mm 9.9 10.3 Max 16 _______9 3.95 1 1000000 8 1.27 *0.22 ± 0.03 0.20 ± 0.03 1.75 Max 6.10 + 0.10 1.08 0.635 Max 0° – 8° $0.60^{+0.67}_{-0.20}$ $^{*}0.42 \pm 0.08 \over 0.40 \pm 0.06$ 0.15 0.25 (M) Hitachi Code FP-16DN JEDEC Conforms *Dimension including the plating thickness EIAJ Conforms Base material dimension Mass (reference value) 0.15 g

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